



**MICRONOVA**  
*Centre for Micro and Nanotechnology*

# GaAs Medipix 2 Hybrid Pixel Detector

Pasi Kostamo\*, H. Lipsanen

*Micro and Nano Sciences Laboratory, Helsinki University of Technology, Espoo, Finland*

S. Nenonen, J. Nieminen, H. Andersson  
*Oxford Instruments Analytical Oy, Espoo, Finland*

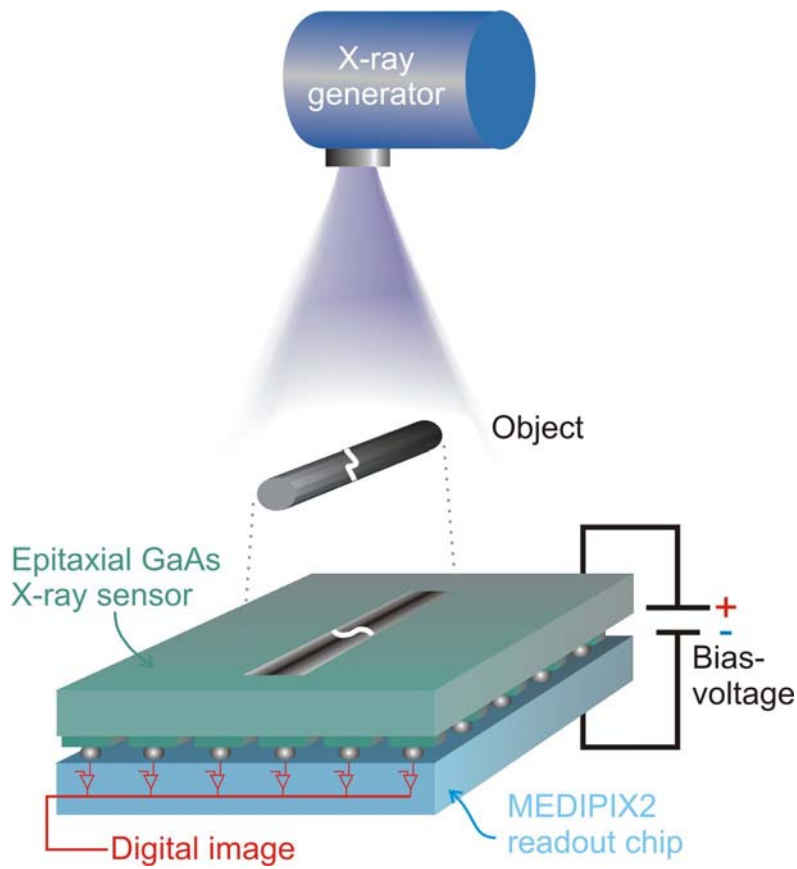
*L. Tlustos, M. Campbell*  
*CERN, Geneva, Switzerland*

S. Vähänen  
*VTT, Espoo, Finland*

\*e-mail: [pasi.kostamo@tkk.fi](mailto:pasi.kostamo@tkk.fi)



# Detector System Schematic



- All epitaxial GaAs sensor
- Thickness 110  $\mu\text{m}$
- Medipix2 photon counting read out chip \*

- 256 x 256 (=65536) pixels
- 55 x 55  $\mu\text{m}^2$  pixel size
- Active area  $\sim 2\text{cm}^2$
- Positive or negative signal input

\* X. Llopart, et. al., Nuclear Science, IEEE Transactions on, vol 49, Issue 5, Oct. 2002 pp. 2279 – 2283v



# Why GaAs?

- Better electrical properties (mobility, band gap) than Si
- Absorption efficiency of GaAs for X-rays is significantly better at 10-100 keV compared to silicon
- E.g. Si 700  $\mu\text{m}$  and GaAs 300  $\mu\text{m}$  @ 50 keV  $\gg$  GaAs absorbs 10x more



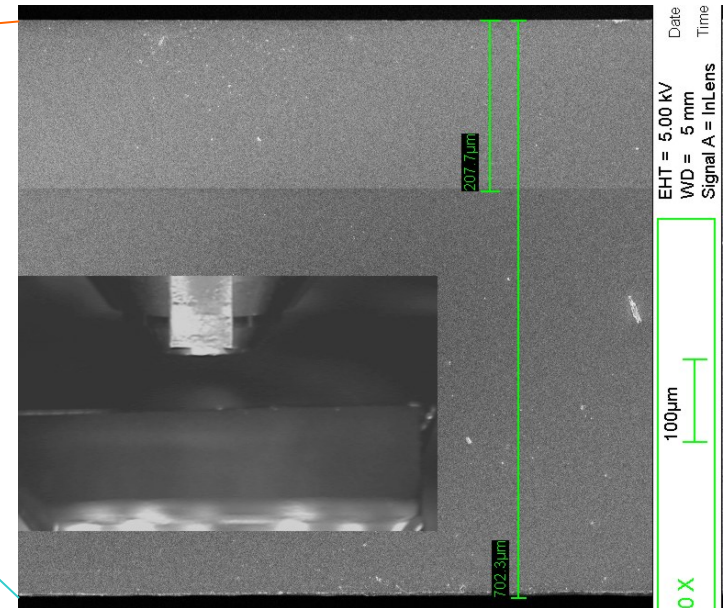
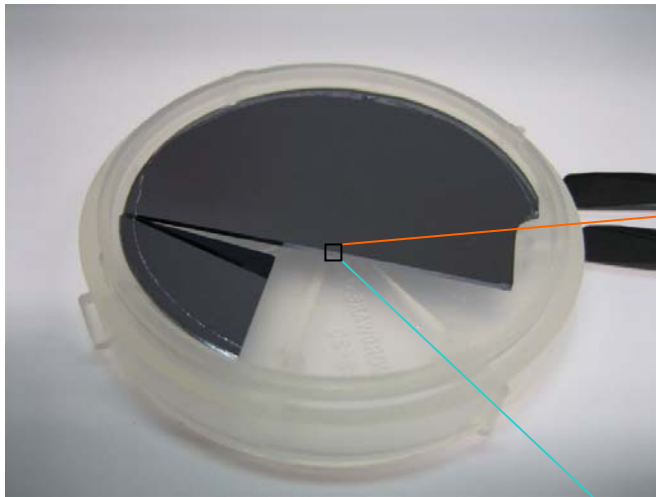
# Epi-GaAs Material

- Hydride vapor phase epitaxy
- High purity and low defect concentration
- Relatively high growth rate up to  $\sim 50 \mu\text{m/h}$ 
  - Epi-layer thickness typically  $> 200 \mu\text{m}$
- Energy resolution 200-250 eV @ 5,9 keV with pad type detectors
- Depletion width max  $\sim 200 \mu\text{m}$  (@  $-20^\circ\text{C}$ )
- Good charge collection efficiency



# Epi-GaAs Material

HVPE GaAs on 50mm substrate



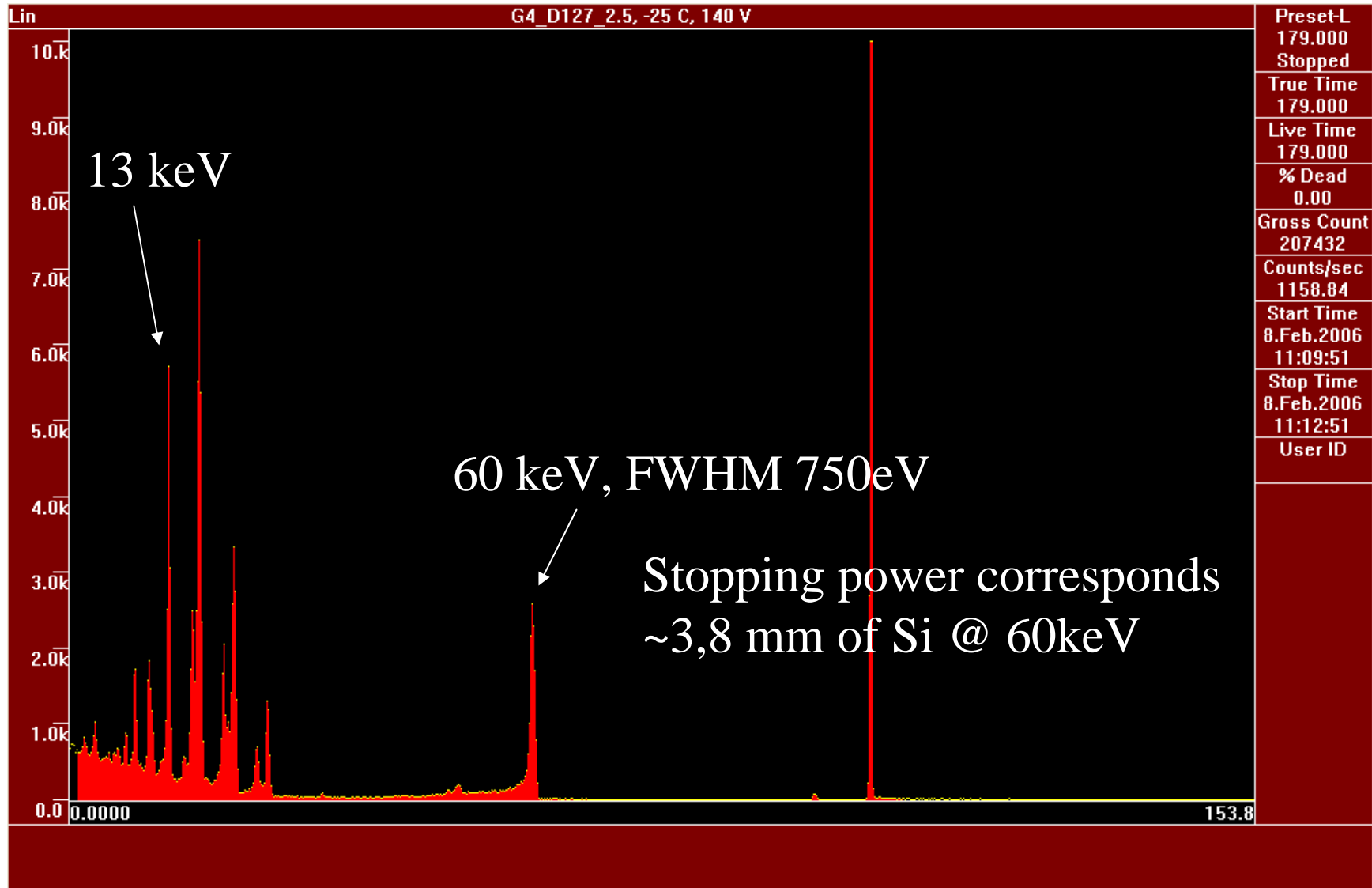
p+ epi-GaAs ~2µm

intrinsic epi-GaAs ~200µm

Substrate ~500µm



# Am-241 Spectrum (pad detector)

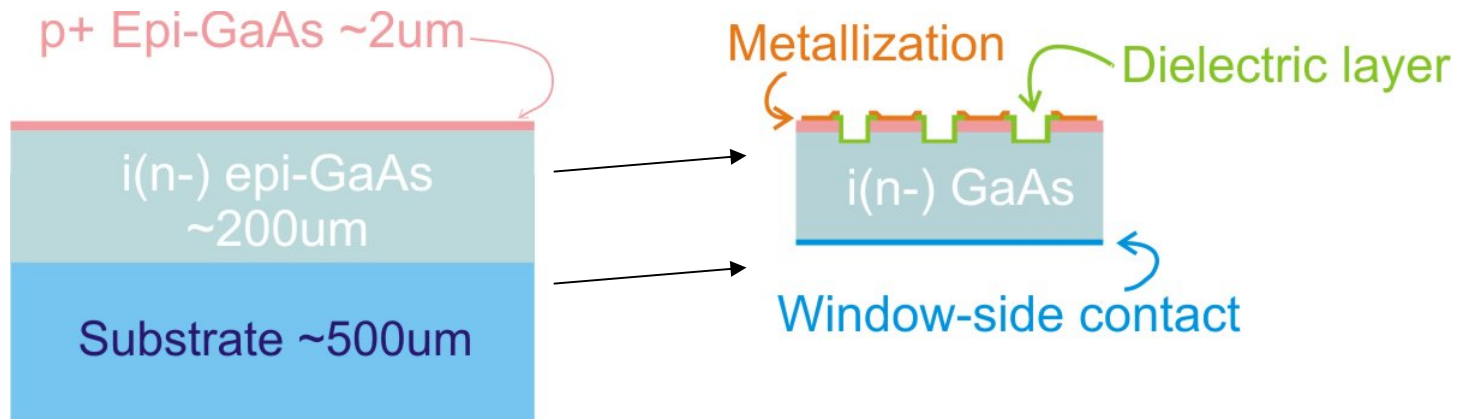




# Thin Detector Processing

Different processing schemes under study but in general

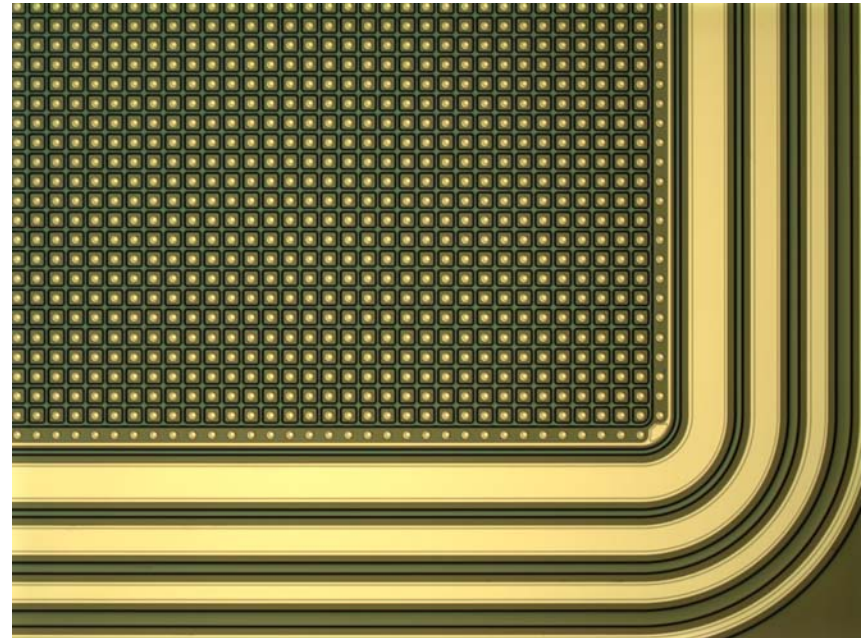
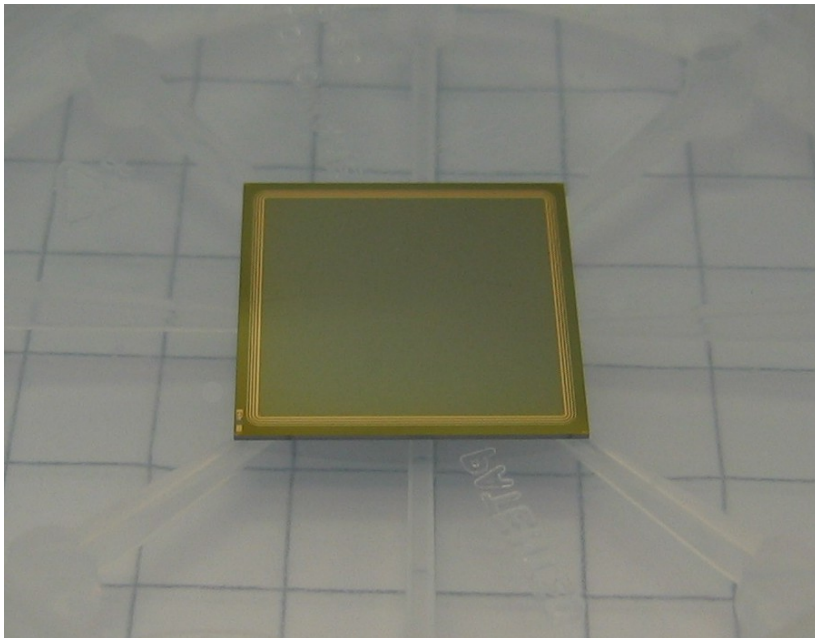
1. Cleaning
2. Mesa etching (ICP-RIE)
3. Passivation
4. Metallization
5. Thinning (target  $<200 \mu\text{m}$ )
6. X-ray window metallization





# Micrographs of the sensor

- Process for manufacture of thin ( $\sim 100\mu\text{m}$ ) all epitaxial sensors developed
- Good quality sensors obtained

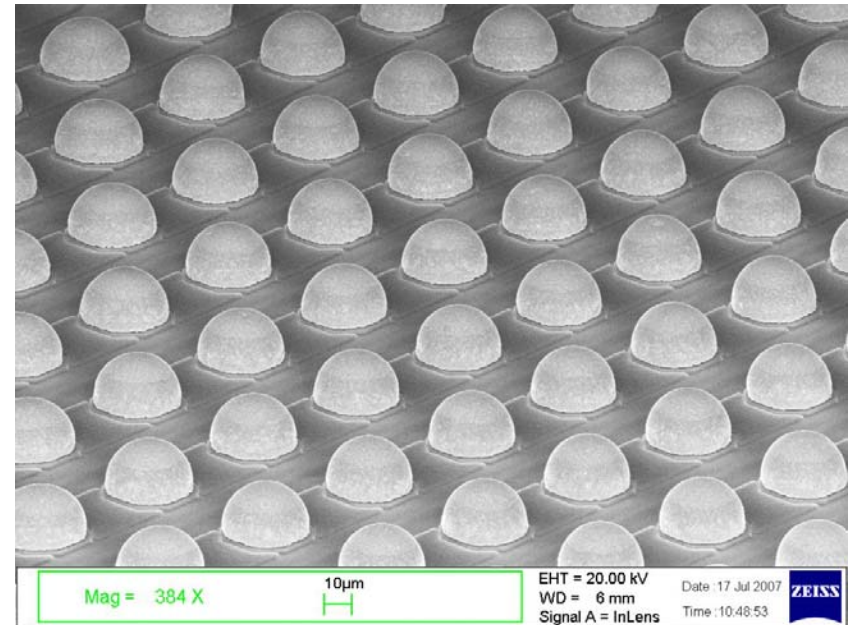
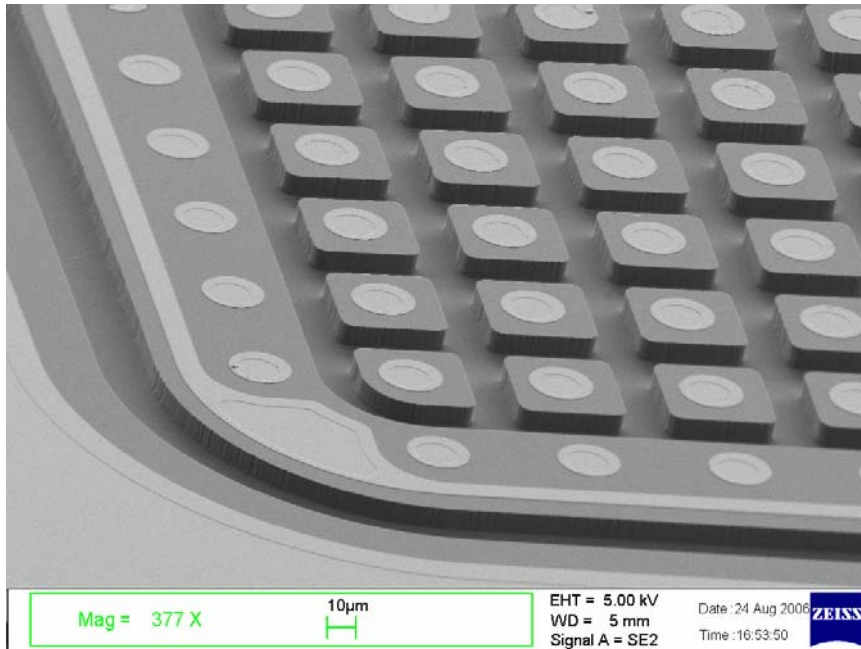




# Bump bonding



- Bump bonding was done with Karl Süss FC150 Flip Chip Bonding Tool at VTT
- Bumps only on the read out chip
- Pb-Sn eutectic solder was used for bonding



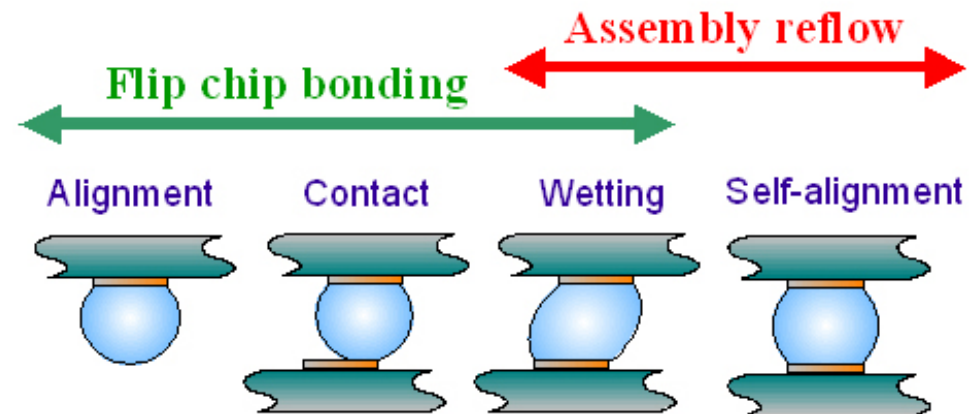


# Bump Bonding



## Process flow

- Preliminary alignment
- Detector and readout chips are adjusted exactly parallel
  - Sensor was not planar
- Lateral alignment (x,y, q)
- Thermo compression of softened bumps
- Cooling
- Assembly reflow

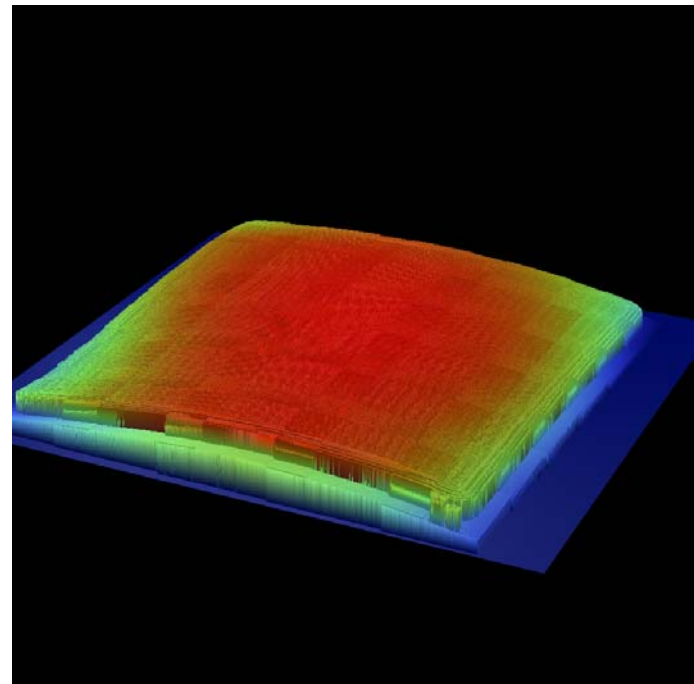
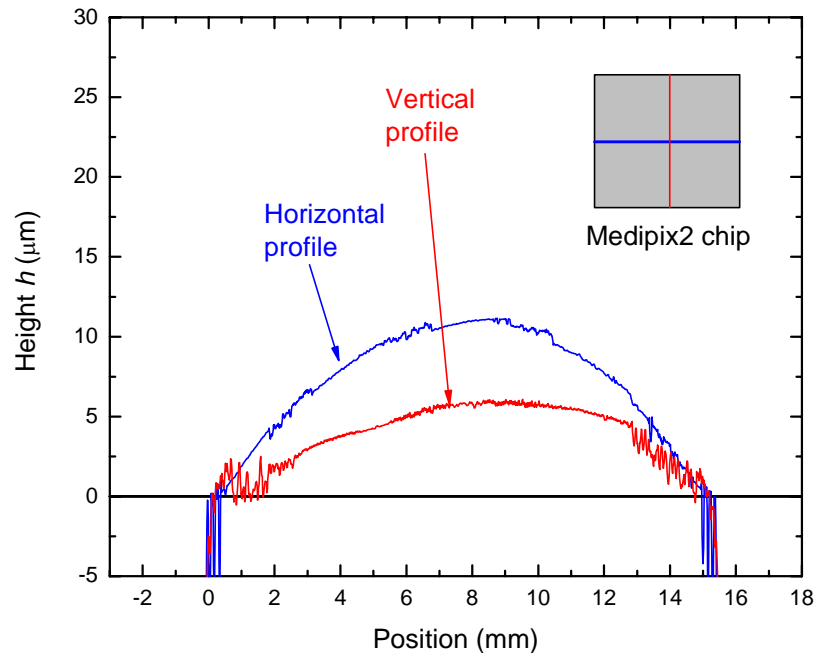


\* S. Savolainen-Pulli, et. al., Experiences in flip chip production of radiation detectors, Nuclear Instruments and Methods in Physics Research A 565 (2006) 314–319



# Profile of the Pixelated Side

- The bow is due to inhomogeneous growth rate
- Not a problem for small component size

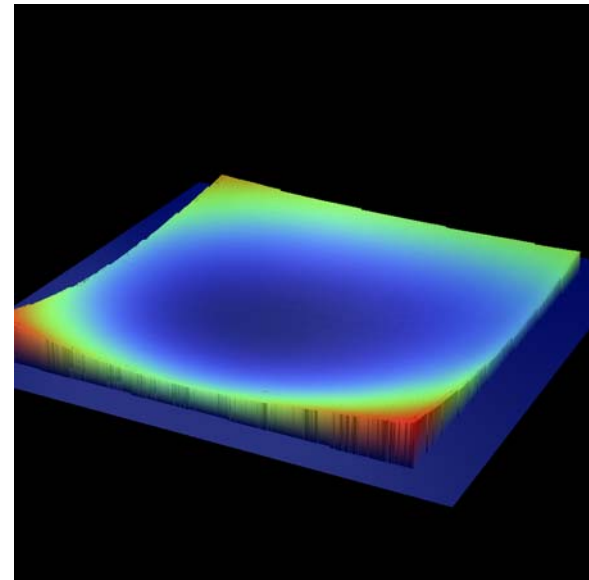




# Profile of the X-ray Window Side

- The sensor element was fixed with thermo wax to a glass substrate
- Stress exists in the epi-layer
- The sample may have been strained during lapping

Bowing is order of  $5 \mu\text{m}$  at the window side





# Thermal expansion

- Coefficients of thermal expansion
  - $\alpha_{\text{GaAs}} = 5,73 \cdot 10^{-6} \text{ cm}^{-1}$
  - $\alpha_{\text{Si}} = 2,60 \cdot 10^{-6} \text{ cm}^{-1}$
- Dimensions of the detector element and readout chip  
 $1,4 \cdot 1,4 \text{ cm}^2$
- Temperature during thermo compression  $170^\circ\text{C}$
- $\Delta L = 6,6 \text{ }\mu\text{m}$
- Some compensation could be applied to the pixel spacing in the sensor chip

Reflow temperature for Pb-Sn solder  $210^\circ\text{C}$  (for In based solder  $180^\circ\text{C}$ )



# Ready Detector

- Flip chip hybridization was successful
- But the sensor was broken in 5 pieces
  - The detector was laid in a package for transportation GaAs sensor facing to adhesive
  - The detector was cracked in 5 pieces during removal



(a)

(b)

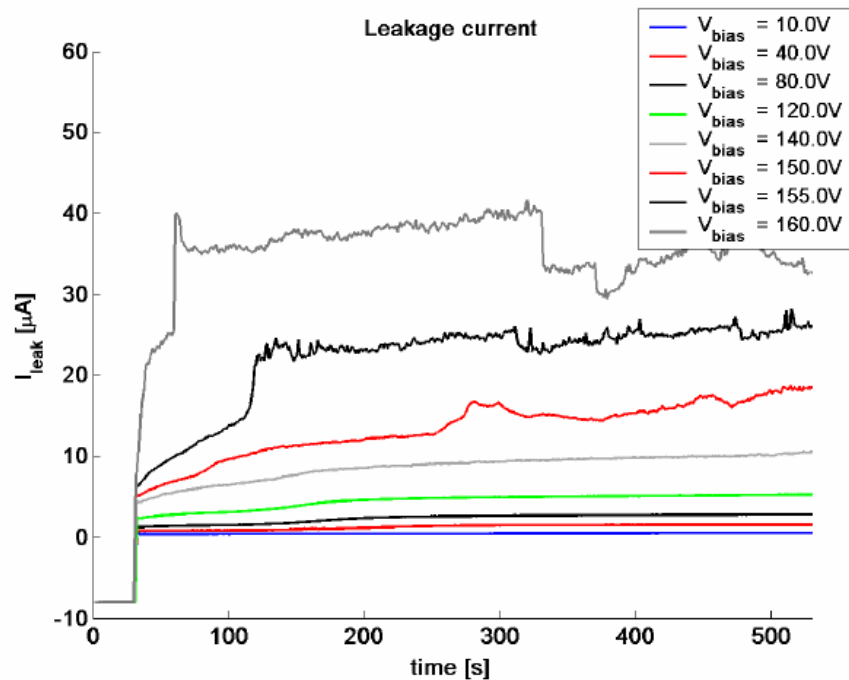


(c)

(d)

# IV Results of MEDIPIX 2 Detector

- Detector was operational despite of the cracking
- Characterization of the component done at CERN





# Conclusions

- Flip chip assembly of Medipix2 readout chip with epitaxial GaAs sensor has been successfully demonstrated
- 2 new detectors have been produced
- Thermal expansion causes problems
- Planarization of the chip would be highly desirable
- Cooling of the detector would enhance the depletion width
- Will the chip take the thermal stress if cooled?